## 1 Scope

The present specifications shall apply to Sanken silicon diode, RM1C.

## 2 Outline

Туре	Silicon Rectifier Diode (Mesa type)				
Structure	Resin Molded Flammability: UL94V-0 (Equivalent)				
Applications	Commercial Frequency Rectification, etc				

## 3 Absolute maximum ratings

3 Abs	olute maximum ratings				.017
	Transient PleadorReverse Voltage	synntø <sub>®</sub> l <sub>M</sub>	Unit√	Rating	Conditions
1	TransikerReParkeRevolungeVoltage	V <sub>R</sub> M <sub>RM</sub>	v v	1050	
2	PeakvaragerFoNotatageurrent	V <sub>R</sub> IM(AV)	V A	1000	
3	Av <b>BeakeStrogevEvor@ardeO</b> urrent	I <sub>F(AF)SM</sub>	A A	0.8	Refer to derating curve in Section 6
4	Peak Surge Forward Current	I <sub>FSM</sub>	А	40	10ms. Half sine wave, one shot
5	Junction Temperature	$T_j$	°C	-40 to +150	
6	Storage Temperature	T <sub>stg</sub>	°C	-40 to +150	

## 4 Electrical characteristics (Ta=25°C, unless otherwise specified)

No.	Item	Symbol	Unit	Rating	Conditions
1	Forward Voltage Drop	$V_{\rm F}$	v	1.2 max.	I <sub>F</sub> =1.0A
2	Reverse Leakage Current	I <sub>R</sub>	μΑ	5 max.	V <sub>R</sub> =V <sub>RM</sub>
3	Reverse Leakage Current Under High Temperature	$H \cdot I_R$	μΑ	100 max.	V <sub>R</sub> =V <sub>RM</sub> , T <sub>j</sub> =100°C
4	Thermal Resistance	R <sub>th(j-l)</sub>	°C/W	15 max.	Between Junction and Lead



- 7 Package information
  - 7-1Package type, physical dimensions and material

